FINAL

Am27C010

1 Megabit (128 K x 8-Bit) CMOS EPROM

DISTINCTIVE CHARACTERISTICS

- **Fast access time**
  - — Speed options as fast as 45 ns
- **Low power consumption**
  - — 20 µA typical CMOS standby current
- **JEDEC-approved pinout**
- **Single +5 V power supply**
- **±10% power supply tolerance standard**
- **100% Flashrite™ programming**
  - — Typical programming time of 16 seconds
- **Latch-up protected to 100 mA from –1 V to V_{CC} + 1 V**
- **High noise immunity**
- **Versatile features for simple interfacing**
  - — Both CMOS and TTL input/output compatibility
  - — Two line control functions
- **Standard 32-pin DIP, PDIP, and PLCC packages**

GENERAL DESCRIPTION

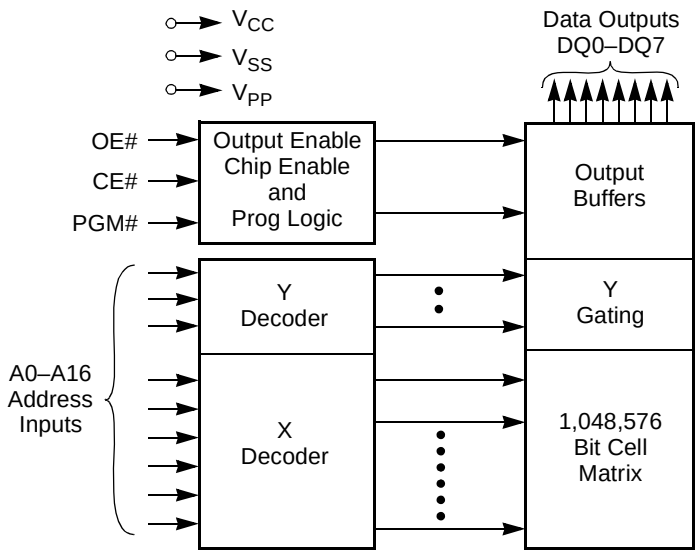
The Am27C010 is a 1 Megabit, ultraviolet erasable programmable read-only memory. It is organized as 128K words by 8 bits per word, operates from a single +5 V supply, has a static standby mode, and features fast single address location programming. Products are available in windowed ceramic DIP packages, as well as plastic one time programmable (OTP) PDIP and PLCC packages.

Data can be typically accessed in less than 45 ns, allowing high-performance microprocessors to operate without any WAIT states. The device offers separate Output Enable (OE#) and Chip Enable (CE#) controls, thus eliminating bus contention in a multiple bus microprocessor system.

AMD's CMOS process technology provides high speed, low power, and high noise immunity. Typical power consumption is only 100 mW in active mode, and 100 µW in standby mode.

All signals are TTL levels, including programming signals. Bit locations may be programmed singly, in blocks, or at random. The device supports AMD's Flashrite programming algorithm (100 µs pulses), resulting in a typical programming time of 16 seconds.

BLOCK DIAGRAM



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